

## AOS Semiconductor Product Reliability Report

AOZ8211DI-05, rev C

**Plastic Encapsulated Device** 

ALPHA & OMEGA Semiconductor, Inc <a href="https://www.aosmd.com">www.aosmd.com</a>



This AOS product reliability report summarizes the qualification result for AOZ8211DI-05. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOZ8211DI-05 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

## I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTRB	Temp = 150°C , Vdd=80% of VRWMmax			JESD22-A108	
Precondition (Note A)	168hr 85°C / 85%RH + 3 cycle reflow@260°C		1386 pcs	0	JESD22-A113
HAST	130°C , 85%RH, 33.3 psia, Vdd = 80% of VRWMmax	96 hours	462 pcs	0	JESD22-A110
Autoclave	121°C , 29.7psia, RH=100%	96 hours	462 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air	250 / 500 cycles	462 pcs	0	JESD22-A104

**Note:** The reliability data presents total of available generic data up to the published date. Note A: MSL (Moisture Sensitivity Level) 1 based on J-STD-020

## II. Reliability Evaluation

FIT rate (per billion): 7.63 MTTF = 14960 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

**Failure Rate** =  $\text{Chi}^2 \times 10^9 / [2 \text{ (N) (H) (Af)}] = 7.63$ **MTTF** =  $10^9 / \text{FIT} = 14960 \text{ years}$ 

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from burn-in tests

**H** = Duration of burn-in testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = Exp [Ea / k (1/Tj u - 1/Tj s)]

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u =The use junction temperature in degree (Kelvin), K = C+273.16

**k** = Boltzmann's constant, 8.617164 X 10<sup>-5</sup>eV / K